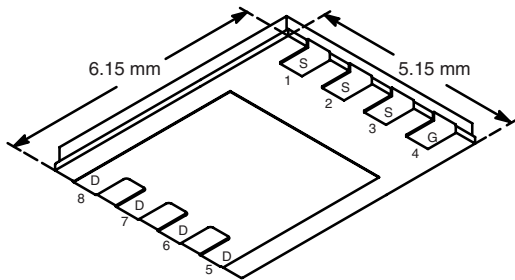




## N-Channel 80 V (D-S) MOSFET

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A) <sup>a</sup>	Q <sub>g</sub> (Typ.)
80	0.0059 at V <sub>GS</sub> = 10 V	60	23 nC
	0.0067 at V <sub>GS</sub> = 7.5 V	60	
	0.0085 at V <sub>GS</sub> = 4.5 V	60	

PowerPAK® SO-8



Bottom View

Ordering Information: SiR880DP-T1-GE3 (Lead (Pb)-free and Halogen-free)

### FEATURES

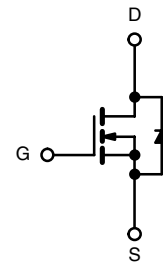
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- 100 % R<sub>g</sub> Tested
- 100 % UIS Tested
- Compliant to RoHS Directive 2002/95/EC



RoHS  
COMPLIANT  
HALOGEN  
FREE

### APPLICATIONS

- Fixed Telecom
- POL
- DC/DC Converter
- Primary Side Switch



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T <sub>A</sub> = 25 °C, unless otherwise noted			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	80	V
Gate-Source Voltage	V <sub>GS</sub>	± 20	
Continuous Drain Current (T <sub>J</sub> = 150 °C)	I <sub>D</sub>	T <sub>C</sub> = 25 °C	60 <sup>a</sup>
		T <sub>C</sub> = 70 °C	60 <sup>a</sup>
		T <sub>A</sub> = 25 °C	23 <sup>b, c</sup>
		T <sub>A</sub> = 70 °C	18.4 <sup>b, c</sup>
Pulsed Drain Current	I <sub>DM</sub>	100	A
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C	
		T <sub>A</sub> = 25 °C	5.6 <sup>b, c</sup>
Single Pulse Avalanche Current	I <sub>AS</sub>	35	mJ
Single Pulse Avalanche Energy	E <sub>AS</sub>	61	
Maximum Power Dissipation	P <sub>D</sub>	T <sub>C</sub> = 25 °C	104
		T <sub>C</sub> = 70 °C	66.6
		T <sub>A</sub> = 25 °C	6.25 <sup>b, c</sup>
		T <sub>A</sub> = 70 °C	4.0 <sup>b, c</sup>
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	°C
Soldering Recommendations (Peak Temperature) <sup>d, e</sup>		260	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>b, f</sup>	t ≤ 10 s	R <sub>thJA</sub>	15	20	°C/W
Maximum Junction-to-Case (Drain)	Steady State	R <sub>thJC</sub>	0.9	1.2	

Notes:

- Package limited.
- Surface Mounted on 1" x 1" FR4 board.
- t = 10 s.
- See Solder Profile ([www.vishay.com/ppg?73257](http://www.vishay.com/ppg?73257)). The PowerPAK SO-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.
- Maximum under Steady State conditions is 54 °C/W.

SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted							
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit	
<b>Static</b>							
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	80			V	
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$		36		mV/ $^\circ\text{C}$	
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			- 5.8			
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1.2		2.8	V	
Gate-Source Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA	
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 80\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{A}$	
		$V_{DS} = 80\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			10		
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	30			A	
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 20\text{ A}$		0.0049	0.0059	$\Omega$	
		$V_{GS} = 7.5\text{ V}, I_D = 20\text{ A}$		0.0054	0.0067		
		$V_{GS} = 4.5\text{ V}, I_D = 15\text{ A}$		0.0070	0.0085		
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 10\text{ V}, I_D = 20\text{ A}$		64		S	
<b>Dynamic<sup>b</sup></b>							
Input Capacitance	$C_{iss}$	$V_{DS} = 40\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		2440		pF	
Output Capacitance	$C_{oss}$			1525			
Reverse Transfer Capacitance	$C_{rss}$			100			
Total Gate Charge	$Q_g$	$V_{DS} = 40\text{ V}, V_{GS} = 10\text{ V}, I_D = 20\text{ A}$		49	74	nC	
		$V_{DS} = 40\text{ V}, V_{GS} = 7.5\text{ V}, I_D = 20\text{ A}$		37.2	56		
Gate-Source Charge	$Q_{gs}$	$V_{DS} = 40\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 20\text{ A}$		23	35		
			Gate-Drain Charge	$Q_{gd}$			7.6
					9.2		
Gate Resistance	$R_g$		$f = 1\text{ MHz}$	0.4	2.1	4.2	$\Omega$
Turn-On Delay Time	$t_{d(on)}$		$V_{DD} = 40\text{ V}, R_L = 2\text{ }\Omega$ $I_D \cong 20\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$		12	24	ns
Rise Time	$t_r$			10	20		
Turn-Off Delay Time	$t_{d(off)}$			38	70		
Fall Time	$t_f$			11	22		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 40\text{ V}, R_L = 2\text{ }\Omega$ $I_D \cong 20\text{ A}, V_{GEN} = 4.5\text{ V}, R_g = 1\text{ }\Omega$		30	55		
Rise Time	$t_r$			26	50		
Turn-Off Delay Time	$t_{d(off)}$			40	75		
Fall Time	$t_f$			12	24		
<b>Drain-Source Body Diode Characteristics</b>							
Continuous Source-Drain Diode Current	$I_S$	$T_C = 25\text{ }^\circ\text{C}$			60	A	
Pulse Diode Forward Current <sup>a</sup>	$I_{SM}$				100		
Body Diode Voltage	$V_{SD}$	$I_S = 5\text{ A}$		0.75	1.1	V	
Body Diode Reverse Recovery Time	$t_{rr}$	$I_F = 20\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		56	100	ns	
Body Diode Reverse Recovery Charge	$Q_{rr}$			66	120	nC	
Reverse Recovery Fall Time	$t_a$			23		ns	
Reverse Recovery Rise Time	$t_b$			33			

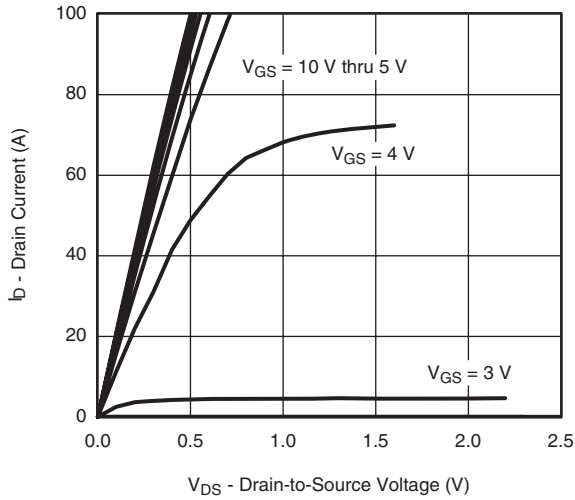
## Notes:

- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .  
b. Guaranteed by design, not subject to production testing.

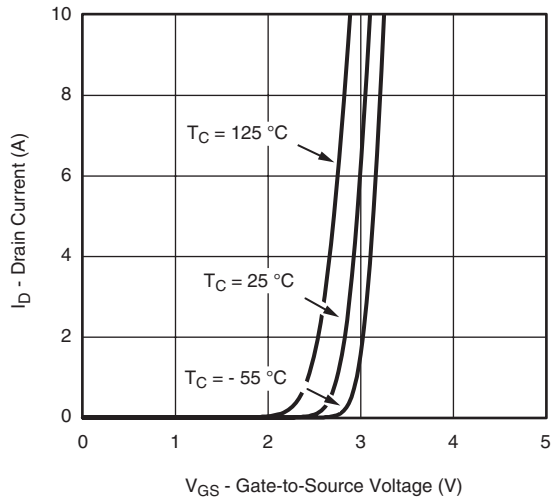
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



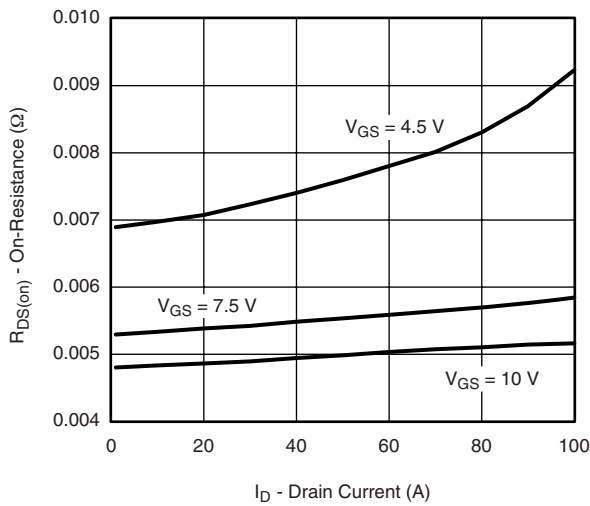
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



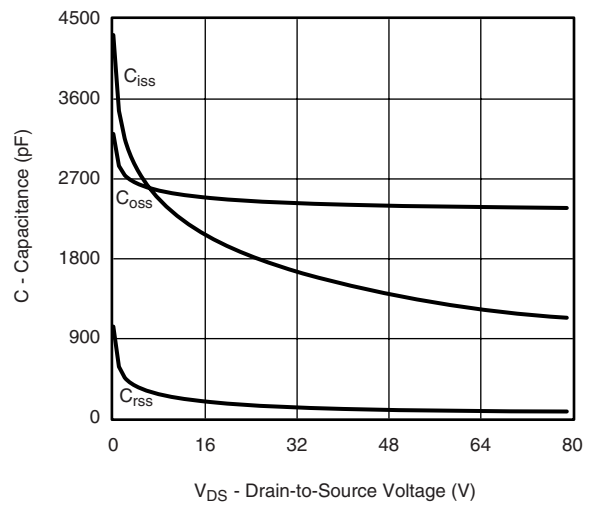
**Output Characteristics**



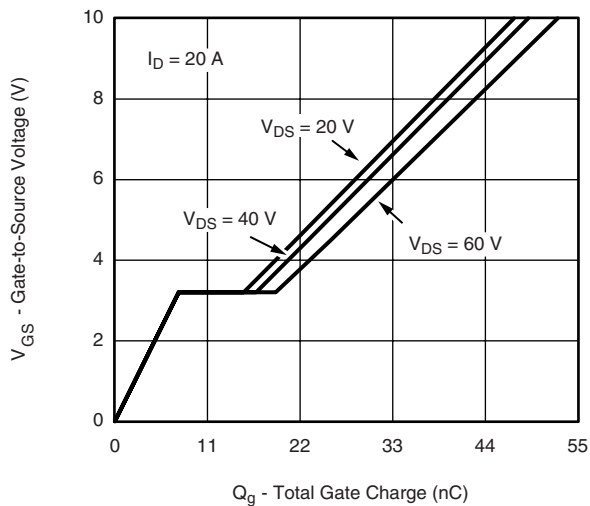
**Transfer Characteristics**



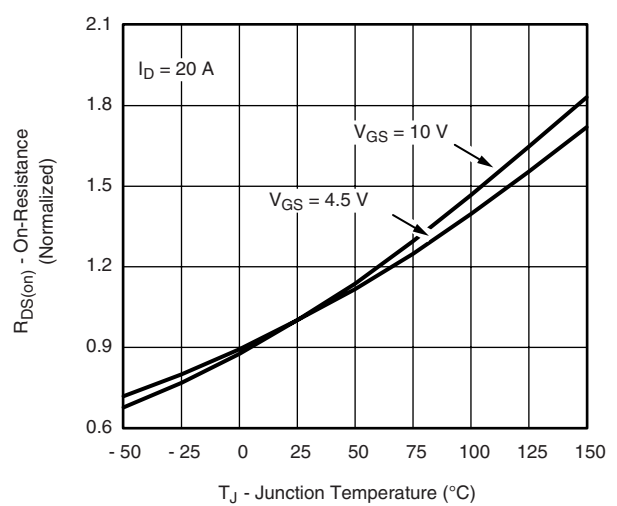
**On-Resistance vs. Drain Current and Gate Voltage**



**Capacitance**



**Gate Charge**



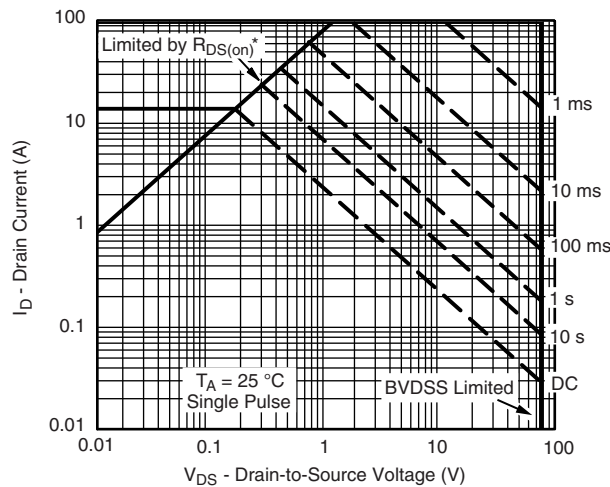
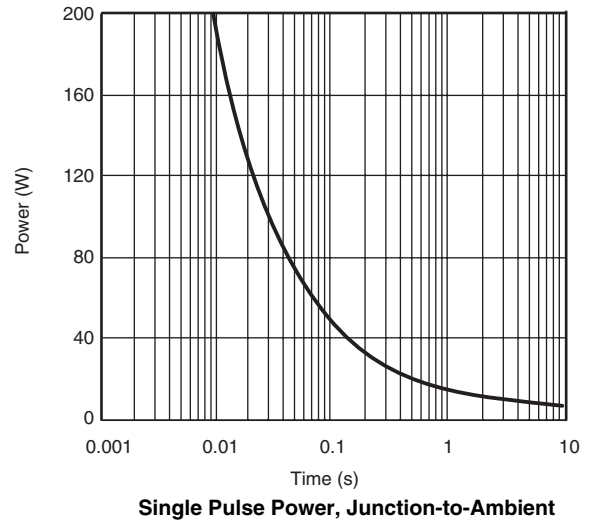
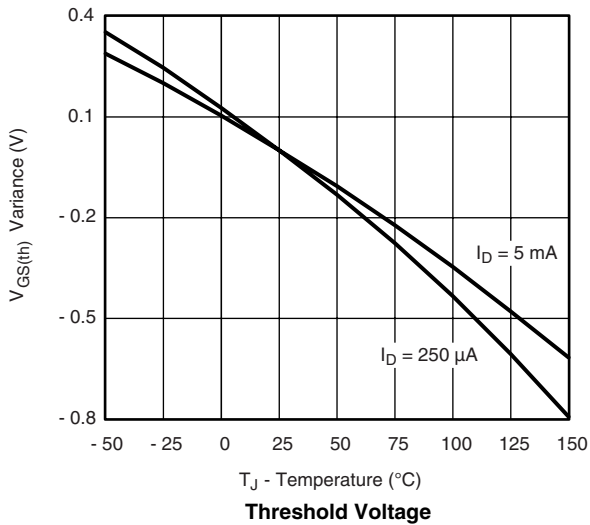
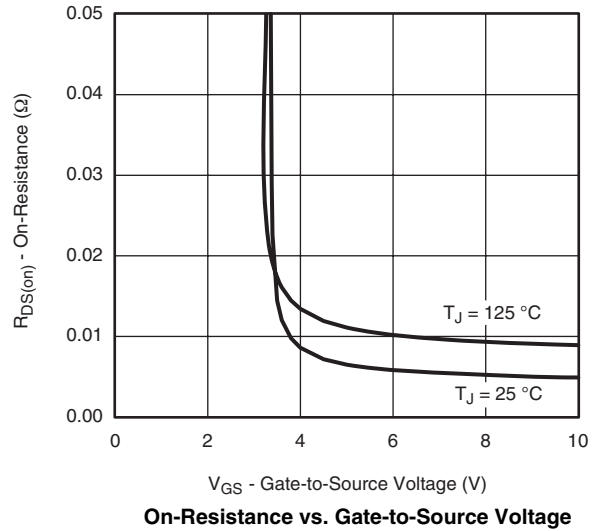
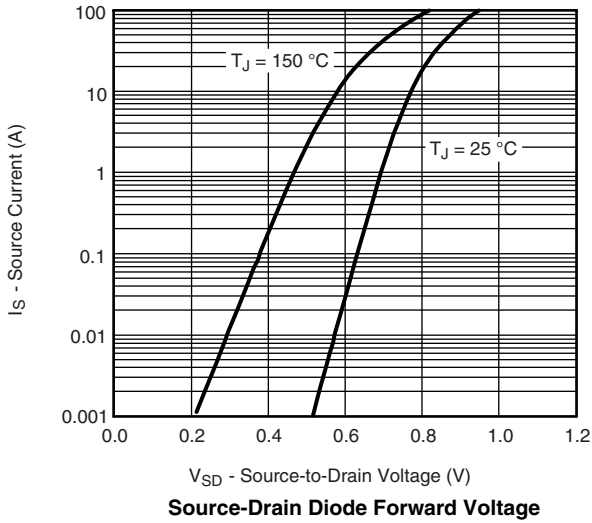
**On-Resistance vs. Junction Temperature**

# SiR880DP

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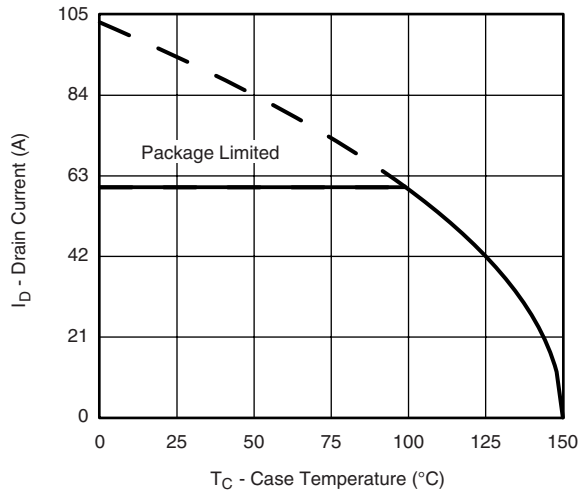
## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



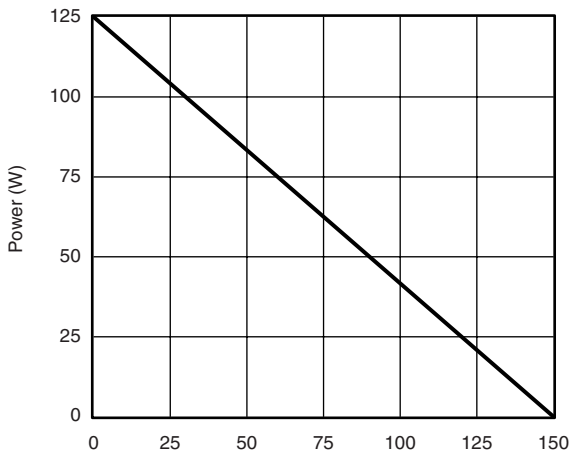
\*  $V_{GS} >$  minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified



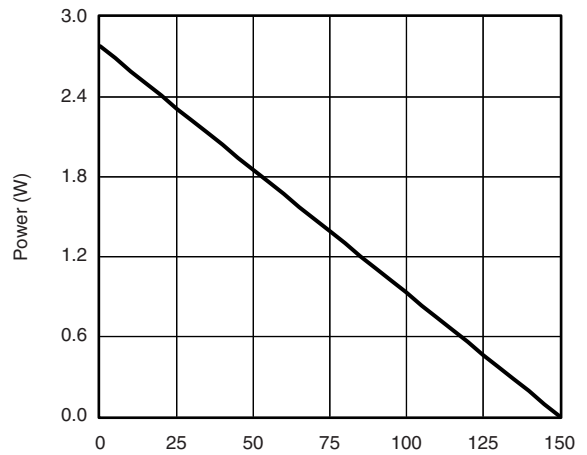
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



**Current Derating\***



**Power, Junction-to-Case**



**Power, Junction-to-Ambient**

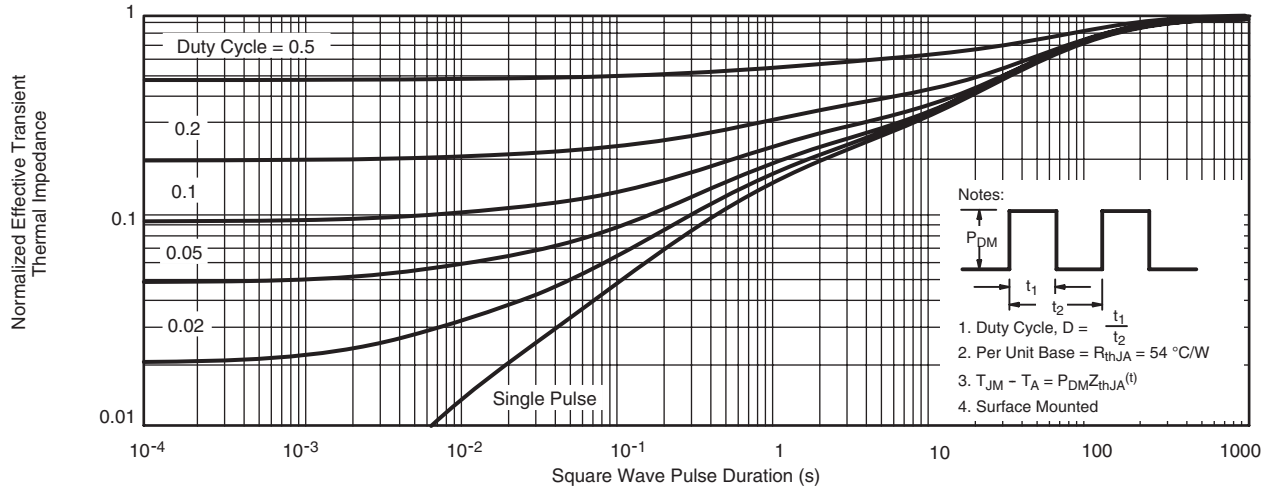
\* The power dissipation  $P_D$  is based on  $T_{J(max)} = 150$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

# SiR880DP

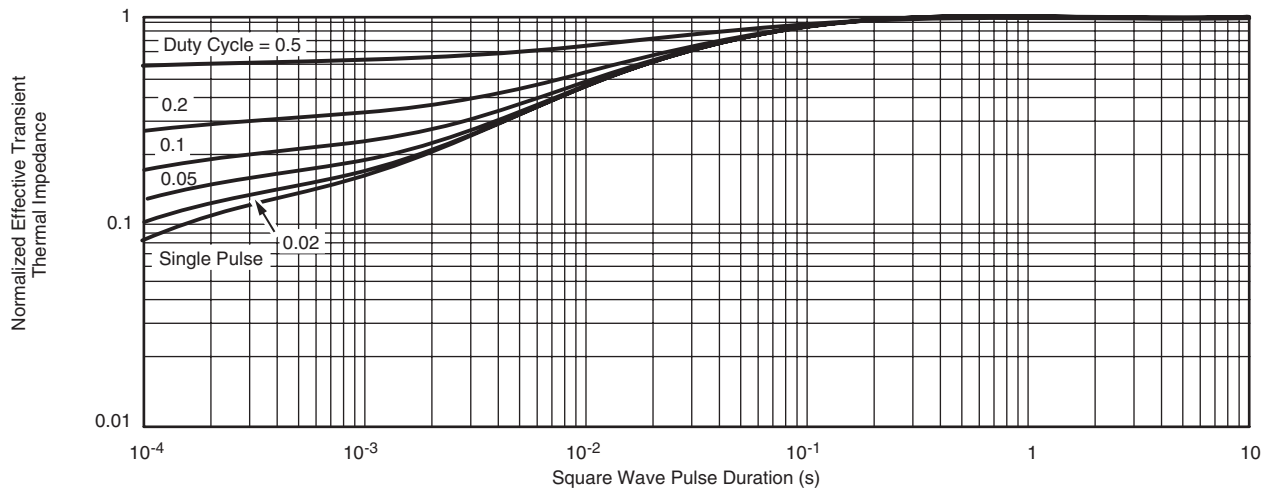
Vishay Siliconix



## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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